# **MPQ2246**



6V, 6A, Configurable-Frequency Synchronous Buck Converter, AEC-Q100 Qualified

#### DESCRIPTION

The MPQ2246 is a configurable-frequency (300kHz to 2.2MHz), synchronous step-down converter. It can achieve up to 6A of continuous output current ( $I_{OUT}$ ) with peak current control for excellent transient response and efficiency performance. The MPQ2246 operates from a 2.7V to 6V input voltage ( $V_{IN}$ ) range, and generates an output voltage ( $V_{OUT}$ ) as low as 0.606V. It is ideal for a wide range of applications, including automotive infotainment, clusters, and telematics, as well as portable instruments.

The MPQ2246 integrates a  $35m\Omega$  high-side MOSFET (HS-FET) and a  $25m\Omega$  synchronous rectifier for high efficiency without an external Schottky diode.

The MPQ2246 can be configured for either advanced asynchronous modulation (AAM) mode or forced continuous conduction mode (FCCM) at light loads. AAM mode provides high efficiency by reducing switching losses at light loads, while FCCM has a controllable frequency and a lower output ripple.

The MPQ2246 offers standard features, including soft start (SS), enable (EN) control, and a power good (PG) indicator. In addition, the MPQ2246 provides over-current protection (OCP) with valley current detection to avoid current runaway, short-circuit protection (SCP), reliable over-voltage protection (OVP), and autorecovery thermal protection.

With internal compensation, the MPQ2246 requires a minimal number of readily available, standard external components. It is available in a QFN-9 (3mmx3mm) package, and is AEC-Q100 qualified.

#### **FEATURES**

- Cool Thermals:
  - Low-Ohmic MPS BCD FET Technology
- Reduces Board Size and BOM:
  - Integrated Compensation Network
  - Available in a Small QFN-9 (3mmx3mm)
     Package
- Additional Features:
  - Adjustable Output Voltage (V<sub>OUT</sub>) from 0.606V
  - High-Efficiency Synchronous Mode Control
  - Configurable Frequency Up to 2.2MHz
  - Low Current in Shutdown Mode
  - 100% Duty Cycle Operation
  - Selectable Advanced Asynchronous Modulation (AAM) Mode or Forced Continuous Conduction Mode (FCCM)
  - External Soft Start (SS)
  - Remote Enable (EN) Control
  - Power Good (PG) Indicator
  - Cycle-by-Cycle Over-Current Protection (OCP)
  - Short-Circuit Protection (SCP)
  - V<sub>IN</sub> Under-Voltage Lockout (UVLO)
  - V<sub>OUT</sub> Over-Voltage Protection (OVP)
  - Thermal Shutdown
  - Available in a Wettable Flank Package
  - Available in AEC-Q100 Grade 1

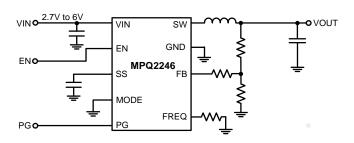
#### **APPLICATIONS**

- Automotive Infotainment
- Automotive Clusters
- Automotive Telematics
- Portable Instruments
- Industrial Supplies
- Battery-Powered Devices

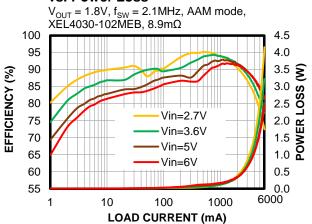
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# TYPICAL APPLICATION



# Efficiency vs. Load Current vs. Power Loss





### ORDERING INFORMATION

| Part Number*       | Package         | Top Marking | MSL Rating** |
|--------------------|-----------------|-------------|--------------|
| MPQ2246GQE-AEC1*** | QFN-9 (3mmx3mm) | See Below   | 1            |

\* For Tape & Reel, add suffix -Z (e.g. MPQ2246GQE-AEC1-Z).

\*\* Moisture Sensitivity Level Rating

\*\*\* Wettable Flank

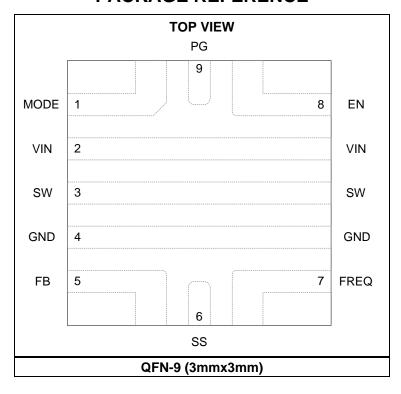
### **TOP MARKING**

BZJY LLLL

BZJ: Product code of MPQ2246GQE-AEC1

Y: Year code LLLL: Lot number

## **PACKAGE REFERENCE**





# PIN FUNCTIONS

| Pin# | Name | Description   |
|------|------|---|
| 1    | MODE | <b>Mode selection.</b> Pull MODE below the 0.4V to select advanced asynchronous modulation (AAM) mode. Pull MODE above the 1.2V to select forced continuous conduction mode (FCCM). Do not leave this pin floating.   |
| 2    | VIN  | <b>Input supply.</b> VIN supplies all power to the converter. To reduce switching spikes, connect a decoupling capacitor to ground, placed as close to the IC as possible.  |
| 3    | SW   | <b>Switch output.</b> Connect SW internally to the high-side and low-side power MOSFETs (HSFET and LS-FET, respectively). Connect SW externally to the output inductor.   |
| 4    | GND  | <b>Ground.</b> Connect GND to larger copper areas on the negative terminals of the input and output capacitors.   |
| 5    | FB   | <b>Feedback point.</b> Negative input of the error amplifier (EA). To set the regulation voltage, connect FB to the tap of an external resistor divider between the output and GND. The power good (PG) and under-voltage lockout (UVLO) circuits use FB to monitor the output voltage (Vout).        |
| 6    | SS   | <b>Soft start.</b> To set the soft-start time (tss) externally, place a capacitor from SS to GND. Float this pin to activate the internal default 1ms tss setting.  |
| 7    | FREQ | <b>Configurable switching.</b> Connect a resistor to GND to set the switching frequency (fsw). See the fsw vs. Rfreq curve on page 12 for more details.   |
| 8    | EN   | <b>Enable input.</b> Pull EN below the 0.4V falling threshold to shut down the chip. Pull EN above the 1.2V rising threshold to enable the chip. There is an internal $1M\Omega$ resistor connected from EN to ground.  |
| 9    | PG   | <b>Power good indicator.</b> The PG output is an open drain that connects to VIN via an internal pull-up resistor. If $V_{FB}$ is within 85% to 115% of the reference voltage ( $V_{REF}$ ), it goes high. If $V_{FB}$ is out of the regulation range, it goes low. Float this pin if it is not used. |

# **ABSOLUTE MAXIMUM RATINGS (1)**

| V <sub>IN</sub>        | 6.5V                               |
|------------------------|------------------------------------|
| V <sub>SW</sub>        | 0.3V (-3V for < 10ns)              |
|                        | to +6.5V (7V for < 10ns)           |
| All other pins         | 0.3V to +6.5V                      |
| Continuous power dissi | pation (T <sub>A</sub> = 25°C) (2) |
|                        | 4.8 W                              |
| Junction temperature   | 150°C                              |
| Lead temperature       | 260°C                              |
| Storage temperature    | 65°C to +150°C                     |
|                        |                                    |

#### ESD Ratings

| Human body model (HBM)   | )Class 2 <sup>(3)</sup> |
|--------------------------|-------------------------|
| Charged device model (CI | DM)Class 2b (4)         |

#### **Recommended Operating Conditions**

| =                                  | _                              |
|------------------------------------|--------------------------------|
| Continuous supply voltage          | e (V <sub>IN</sub> )2.7V to 6V |
| Output voltage (V <sub>OUT</sub> ) | 0.606V to V <sub>IN</sub>      |
| Load current range                 | 0A to 6A                       |
| Operating junction temp (7         | Г <sub>Ј</sub> )               |
|                                    | -40°C to +125°C (5)            |

#### Thermal Resistance $\theta_{JA}$ $\theta_{JC}$

| QFN-9 (3mmx3mm) |      |                        |
|-----------------|------|------------------------|
| JESD51-7        | 61.8 | 5.6°C/W <sup>(6)</sup> |
| EVQ2246-Q-00A   | 30.7 | 5.1°C/W (7)            |

#### Notes:

- 1) Exceeding these ratings may damage the device.
- The maximum allowable power dissipation is a function of the maximum junction temperature T<sub>J</sub> (MAX), the junction-toambient thermal resistance  $\theta_{JA}$ , and the ambient temperature  $T_A$ . The maximum allowable continuous power dissipation at any ambient temperature is calculated by  $P_D$  (MAX) =  $(T_J (MAX) - T_A)$ /  $\theta_{JA}$ . Exceeding the maximum allowable power dissipation can cause excessive die temperature, and the device may go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- Per AEC-Q100-002.
- Per AEC-Q100-011.
- The device is not guaranteed to function outside of the operation conditions. Operating devices at junction temperatures greater than 125°C is possible; contact MPS for details.
- Measured on JESD51-7, 4-layer PCB. The values given in this table are only valid for comparison with other packages and cannot be used for design purposes. These values were calculated in accordance with JESD51-7, and simulated on a specified JEDEC board. They do not represent the performance obtained in an actual application, the value of  $\theta_{JC}$  shows the thermal resistance from junction-to-case bottom.
- Measured on MPS MPQ2246 standard EVB: 6.35cmx6.35cm, 2oz. thick copper, 4-layer PCB. The value of  $\theta_{\text{JC}}$  shows the thermal resistance from junction-to-case top.



# **ELECTRICAL CHARACTERISTICS**

 $V_{IN} = V_{EN} = 3.6V$ ,  $T_J = -40$ °C to +125°C, typical values are at  $T_J = 25$ °C, unless otherwise noted.

| Parameters   | Symbol                     | Condition   | Min   | Тур   | Max   | Units |
|--|----------------------------|---|-------|-------|-------|-------|
| Input Supply and Under-V                               | oltage Lockou              | it (UVLO)   |       |       |       |       |
|  |                            | AAM mode, V <sub>EN</sub> = 2V, no load,  |       | 42    | 50    |       |
| Quiescent supply current                               | IQ                         | $R_{FREQ} = 125k\Omega$ , $T_J = 25^{\circ}C$   |       | 42    | 50    | μA    |
|  |                            | $T_J = -40^{\circ}\text{C to } +125^{\circ}\text{C}$                                    |       |       | 120   | μΑ    |
| Shutdown current                                       | I <sub>SD</sub>            | AAM mode, V <sub>EN</sub> = 0V, T <sub>J</sub> = 25°C                                   |       | 0     | 1     | μΑ    |
| $T_{J} = -40^{\circ}\text{C to } +125^{\circ}\text{C}$ |                            |   |       | 20    | μΑ    |       |
| VIN UVLO rising threshold                              | V <sub>IN_UVLO_VTH-R</sub> |   | 2.3   | 2.5   | 2.7   | V     |
| V <sub>IN</sub> UVLO falling threshold                 | V <sub>IN_UVLO_VTH-F</sub> |   | 2     | 2.15  | 2.3   | V     |
| V <sub>IN</sub> UVLO hysteresis threshold              | VIN_UVLO_HYS               |   |       | 350   |       | mV    |
| <b>Output and Regulation</b>                           |                            |   |       |       |       |       |
| Regulated feedback (FB)                                | \/                         | T <sub>J</sub> = 25°C   | 0.596 | 0.606 | 0.616 | V     |
| voltage  | $V_{FB}$                   | $T_J = -40^{\circ}\text{C to } +125^{\circ}\text{C}$                                    | 0.594 |       | 0.618 | V     |
| FB input current                                       | I <sub>FB</sub>            | V <sub>FB</sub> = 0.63V   |       | 10    | 100   | nA    |
| Output discharge resistor                              | Rdischarge                 |   | 50    | 100   | 150   | Ω     |
| <b>Switches and Frequency</b>                          |                            |   |       |       |       |       |
| High-side MOSFET (HS-<br>FET) on resistance            | R <sub>DS(ON)_</sub> H     | V <sub>IN</sub> = 5V, I <sub>OUT</sub> = 200mA  |       | 35    | 70    | mΩ    |
| Low-side MOSFET (LS-<br>FET) on resistance             | R <sub>DS(ON)_L</sub>      | V <sub>IN</sub> = 5V, I <sub>OUT</sub> = 200mA  |       | 25    | 70    | mΩ    |
| HS-FET leakage current                                 |                            | $V_{EN} = 0V$ , $V_{IN} = 6V$ , $V_{SW} = 6V$ , $T_J = 25$ °C                           |       | 0     | 1     | μΑ    |
|  | IHSW-LKG                   | T <sub>J</sub> = -40°C to +125°C  |       |       | 30    | μA    |
| LO FET L   |                            | V <sub>EN</sub> = 0V, V <sub>IN</sub> = 6V, V <sub>SW</sub> = 0V, T <sub>J</sub> = 25°C |       | 0     | 1     | μA    |
| LS-FET leakage current                                 | ILSW-LKG                   | $T_J = -40^{\circ}\text{C to } +125^{\circ}\text{C}$                                    |       |       | 10    | μΑ    |
| Curitohina fraguanay                                   | £.                         | $R_{FREQ} = 65k\Omega$  | 380   | 450   | 520   | kHz   |
| Switching frequency                                    | f <sub>SW</sub>            | $R_{FREQ} = 9.31k\Omega$  | 1800  | 2100  | 2400  | kHz   |
| Maximum duty cycle                                     | D <sub>MAX</sub>           |   |       | 100   |       | %     |
| Minimum on time (8)                                    | ton_min                    |   |       | 50    |       | ns    |
| Minimum off time (8)                                   | toff_min                   |   |       | 95    |       | ns    |
| Power Good (PG)  |                            |   |       |       |       |       |
| PG sink current capacity                               | V <sub>PG-SINK</sub>       | Sink 0.5mA  |       |       | 300   | mV    |
| PG logic high voltage                                  | V <sub>PG-HIGH</sub>       | V <sub>IN</sub> = 5V  | 4.5   |       |       | V     |
| DO de elitab   | _                          | V <sub>OUT</sub> rising edge  | 40    | 100   | 180   | μs    |
| PG deglitch  | tpg_deglith                | V <sub>OUT</sub> falling edge   | 10    | 25    | 40    | μs    |
| PG upper rising threshold                              | PG <sub>UP_R</sub>         | As a percentage of V <sub>FB</sub>  | 108   | 115   | 122   | %     |
| PG upper hysteresis                                    | PG <sub>UP_HYS</sub>       | As a percentage of V <sub>FB</sub>  |       | 5     |       | %     |
| PG lower rising threshold                              | PG <sub>LOW_R</sub>        | As a percentage of V <sub>FB</sub>  | 80    | 85    | 90    | %     |
| PG lower hysteresis                                    | PG <sub>LOW_HYS</sub>      | As a percentage of V <sub>FB</sub>  |       | 5     |       | %     |
| Enable (EN)  |                            | •   | •     | •     | •     | ,     |
| EN input rising threshold                              | V <sub>EN-RISING</sub>     |   | 1.2   |       |       | V     |
| EN input falling threshold                             | Ven-falling                |   |       |       | 0.4   | V     |
|  |                            | V <sub>EN</sub> = 2V  |       | 2     | 5     | μA    |
| EN input current                                       | I <sub>EN</sub>            | V <sub>EN</sub> = 0V  |       | 0     | 0.5   | μA    |



# **ELECTRICAL CHARACTERISTICS** (continued)

 $V_{IN} = V_{EN} = 3.6V$ ,  $T_J = -40$ °C to +125°C, typical values are at  $T_J = 25$ °C, unless otherwise noted.

| Parameters                              | Symbol                    | Condition                          | Min | Тур | Max  | Units |
|---|---------------------------|------------------------------------|-----|-----|------|-------|
| Mode and Soft Start (SS)                |                           |                                    |     |     |      |       |
| MODE pin rising threshold               | V <sub>MODE-FCCM</sub>    | Into FCCM                          | 1.2 |     |      | V     |
| MODE pin falling threshold              | V <sub>MODE-AAM</sub>     | Into AAM mode                      |     |     | 0.4  | V     |
| Mode input leakage current              | I <sub>MODE</sub>         | Pulled up to 6V                    |     |     | 1    | μΑ    |
| Soft-start charge current               | Iss                       | Vss = 0V                           | 2   | 4   | 6    | μΑ    |
| Default soft-start time                 | tss-default               |                                    |     | 1   |      | ms    |
| Protections                             |                           |                                    |     |     |      |       |
| Peak current limit                      | I <sub>PEAK_LIMIT</sub>   | Sourcing, duty cycle = 40%         | 7.8 | 9.5 | 11.2 | Α     |
| Valley current limit                    | I <sub>VALLEY_LIMIT</sub> |                                    |     | 7   |      | Α     |
| Over-current protection (OCP) timer (8) | tocp                      |                                    |     | 100 |      | μs    |
| Zero-current detection (ZCD) threshold  | Izco                      |                                    |     | 100 |      | mA    |
| Output over-voltage (OV) limit          | OVLIMIT                   | As a percentage of V <sub>FB</sub> |     | 115 |      | %     |
| Thermal shutdown (8)                    | T <sub>SD</sub>           | Temperature rising                 |     | 170 |      | °C    |
| Thermal shutdown hysteresis (8)         | T <sub>SD-HYS</sub>       |                                    |     | 25  |      | °C    |

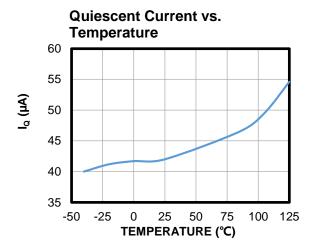
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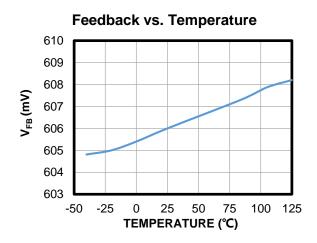
<sup>8)</sup> Guaranteed by design and characterization. Not tested in production.

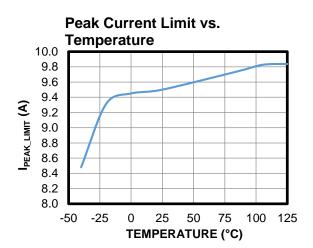


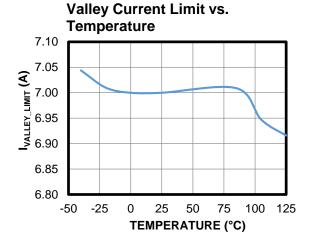
### TYPICAL CHARACTERISTICS

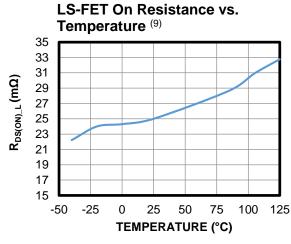
 $V_{IN} = 3.6V$ ,  $T_J = 25$ °C, unless otherwise noted.

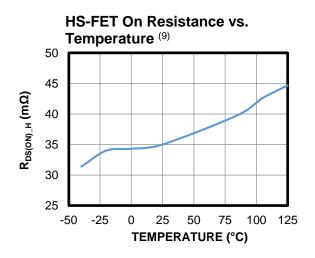










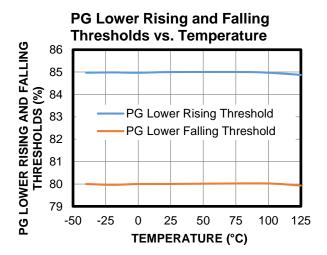


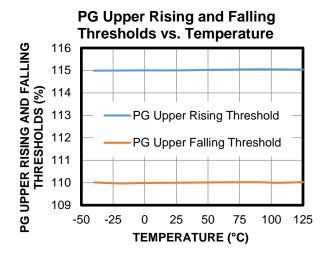
9) This test item is evaluated under  $V_{IN} = 5V$ .

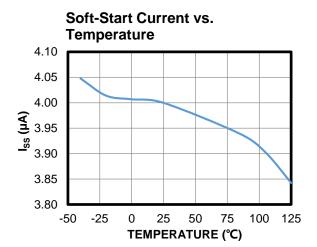


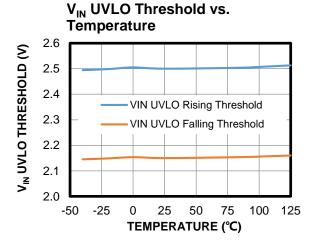
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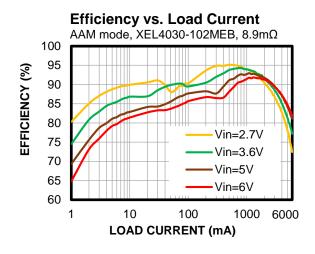


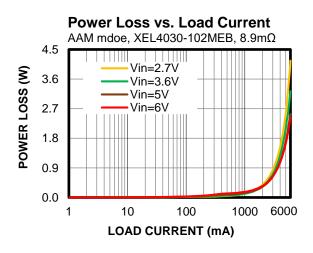


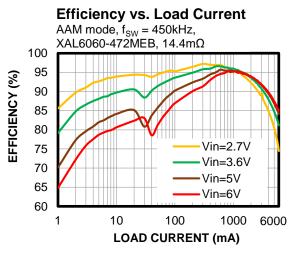


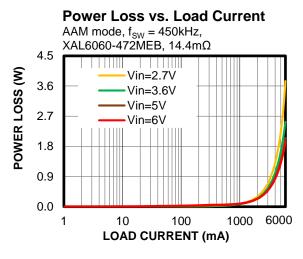


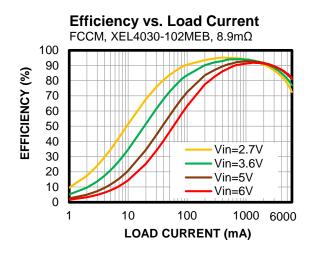
# TYPICAL PERFORMANCE CHARACTERISTICS

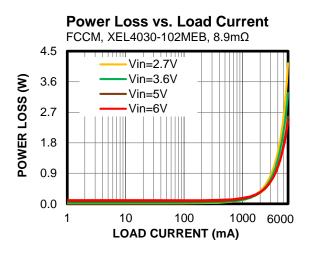






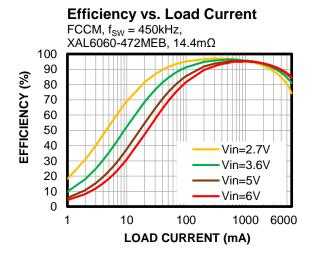


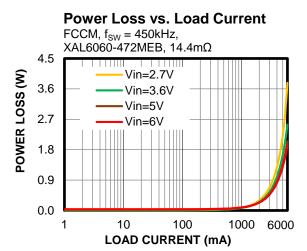


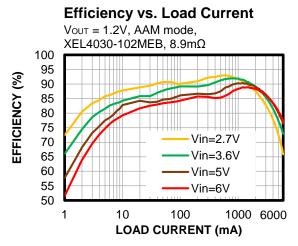


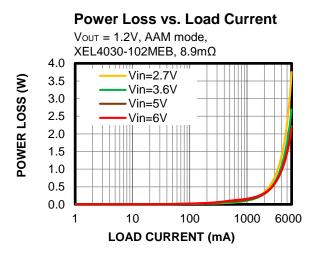


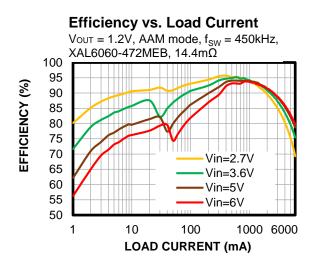
 $V_{IN} = 5V$ ,  $V_{OUT} = 1.8V$ ,  $L = 1\mu H$ ,  $C_{OUT} = 22\mu F$  x 2,  $f_{SW} = 2.1 MHz$ ,  $T_A = 25$ °C, unless otherwise noted.

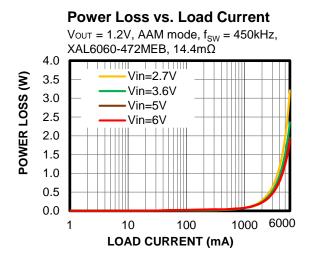






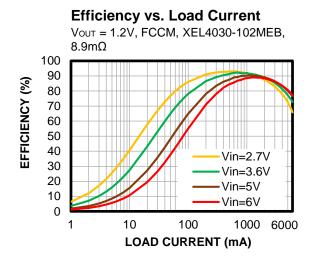


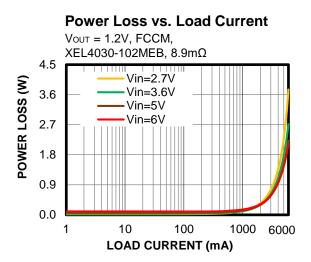


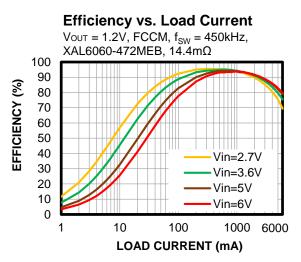


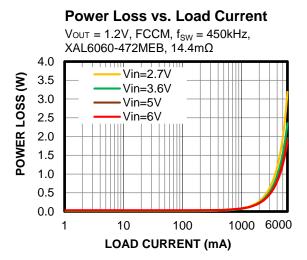
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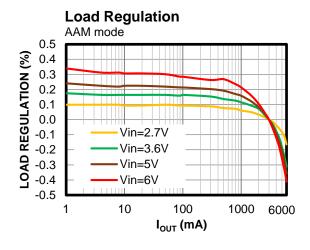


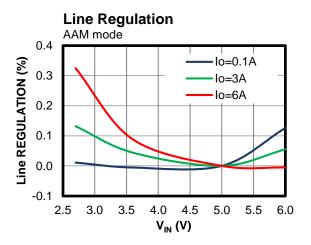




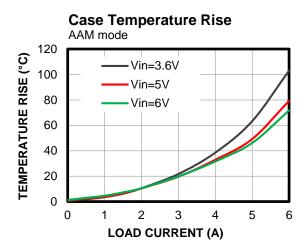


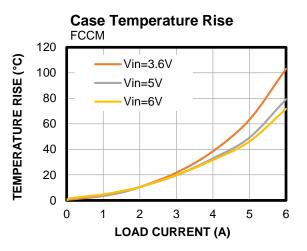


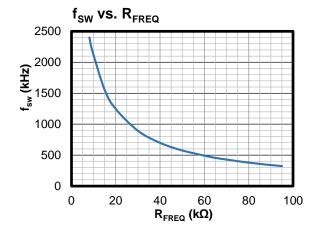






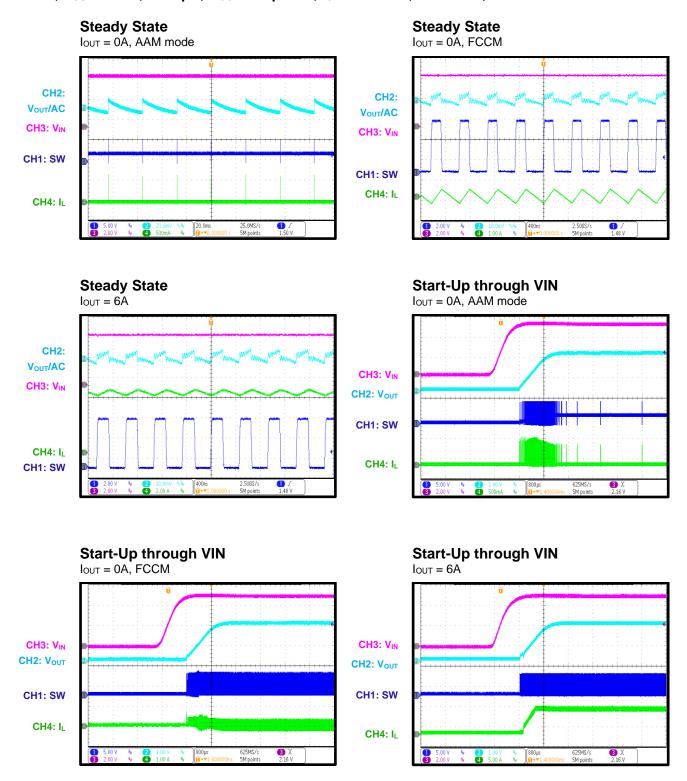




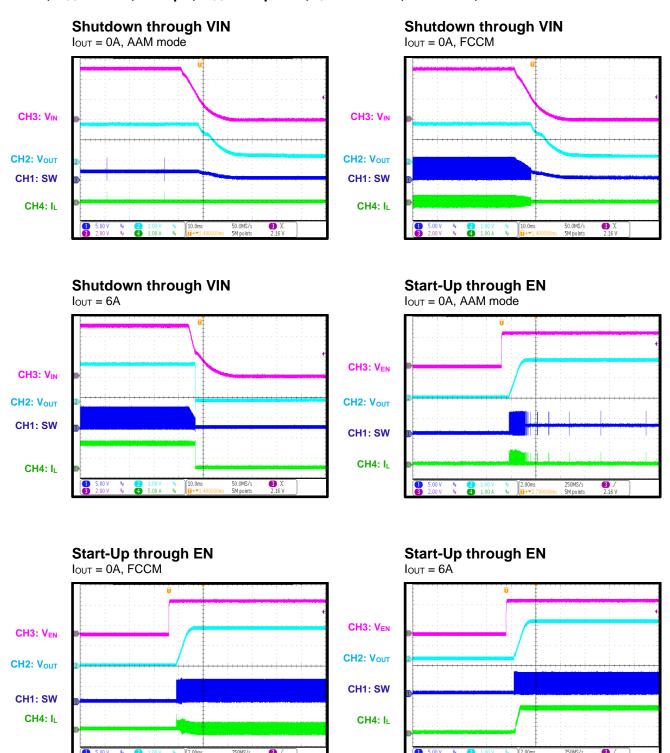




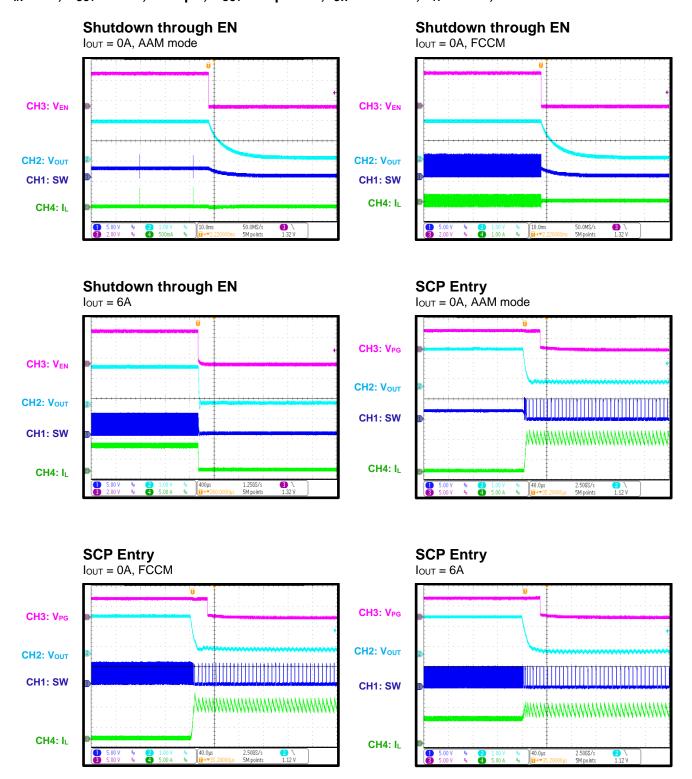
# TYPICAL PERFORMANCE CHARACTERISTICS



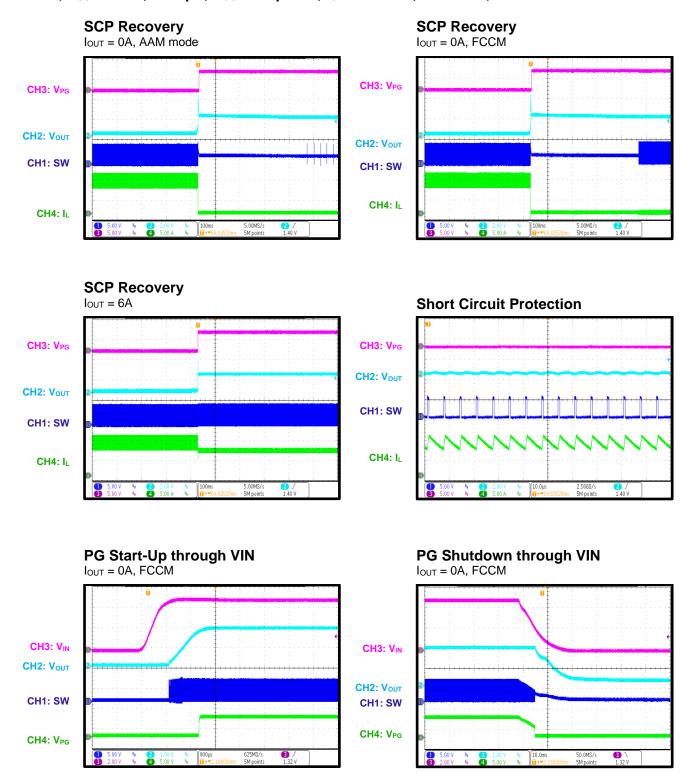




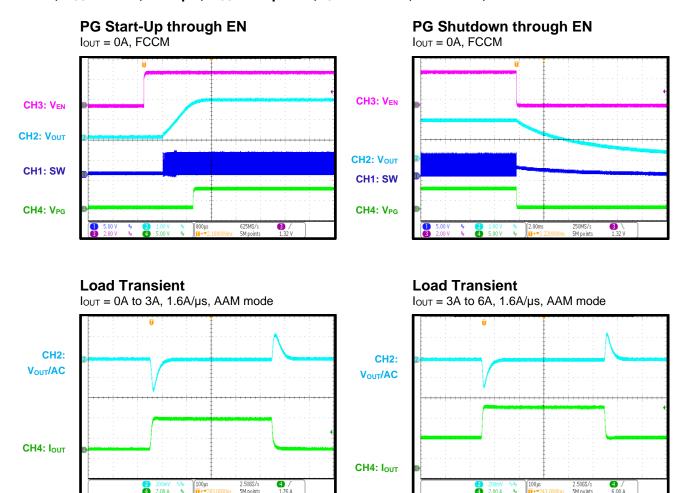






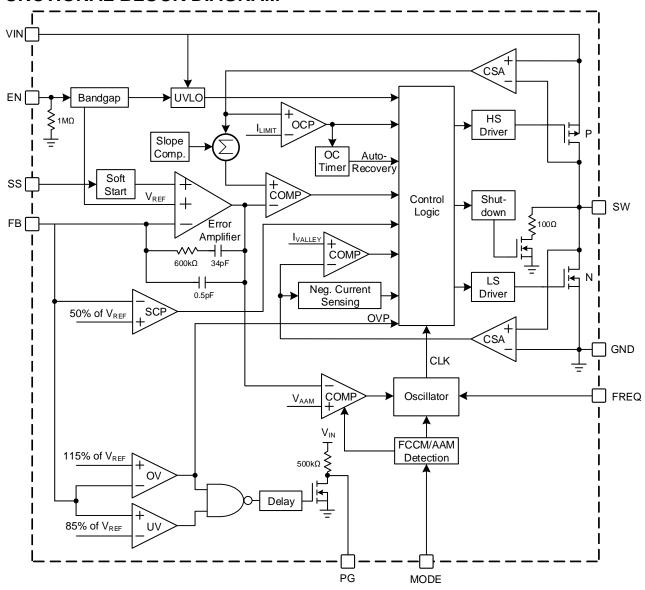








# **FUNCTIONAL BLOCK DIAGRAM**



**Figure 1: Functional Block Diagram** 



# **OPERATION**

The MPQ2246 is a fully integrated, synchronous, rectified, step-down, non-isolated switch-mode converter. It uses peak current mode control with internal compensation for faster transient response and cycle-by-cycle current limiting.

Figure 1 on page 18 shows the block diagram of the device. The MPQ2246 is available with a 2.7V to 6V input voltage ( $V_{\text{IN}}$ ) supply range, and can achieve up to 6A of continuous output current ( $I_{\text{OUT}}$ ), with excellent load and line regulation across an ambient temperature range of -40°C to +125°C. The output voltage ( $V_{\text{OUT}}$ ) can be regulated as low as 0.606V.

The MPQ2246 is optimized for low-voltage portable applications where efficiency and small size are critical. It can operate with up to a 2.2MHz switching frequency ( $f_{SW}$ ), which enables the use of a smaller inductor while still providing excellent efficiency. It also allows for high power conversion efficiency under light-load conditions with advanced asynchronous modulation (AAM) mode.

### **Forced Continuous Conduction Mode (FCCM)**

Pulling MODE high (>1.2V) forces the converter into forced continuous conduction mode (FCCM). In FCCM, the MPQ2246 operates in fixed-frequency, peak current control mode to regulate  $V_{\text{OUT}}$ , regardless of  $I_{\text{OUT}}$ .

An internal clock initiates an FCCM cycle. At the rising edge of the clock, the high-side MOSFET (HS-FET) turns on, and the inductor current ( $I_L$ ) rises linearly to provide energy to the load. The HS-FET remains on until its current reaches the comparator voltage ( $V_{COMP}$ ), which is the output of the internal error amplifier (EA).  $V_{COMP}$  is the difference between the output feedback (FB) voltage ( $V_{FB}$ ) and the internal high-precision reference ( $V_{REF}$ ).  $V_{COMP}$  determines how much energy should be transferred to the load; a higher load current results in a higher  $V_{COMP}$ .

When the HS-FET is off, the low-side MOSFET (LS-FET) turns on immediately and remains on until the next clock starts. During this time, I<sub>L</sub> flows through the LS-FET. To avoid shoot-through, a dead time is inserted to avoid the HS-FET and LS-FET turning on simultaneously. For each turn-on/off period in a switching cycle, the HS-FET remains on or off for a set time limit.

# Advanced Asynchronous Modulation (AAM) Mode

Pulling MODE low (<0.4V) to force the converter into light-load AAM mode. There is an internally fixed AAM threshold voltage ( $V_{AAM}$ ). Under light-load conditions, the value of  $V_{COMP}$  is low. If  $V_{COMP}$  exceeds  $V_{AAM}$ , the MPQ2246 first enters discontinuous conduction mode (DCM) with a fixed frequency, as long as  $I_L$  approaches 0A.

If the load decreases further, or there is no load and  $V_{\text{COMP}}$  drops below  $V_{\text{AAM}}$ , then the internal clock is blocked, and the MPQ2246 skips some pulses. During this time,  $V_{\text{FB}}$  is below  $V_{\text{REF}}$ , so  $V_{\text{COMP}}$  ramps up until it exceeds  $V_{\text{AAM}}$ . Then the internal clock is reset, and the crossover time is used as a benchmark for the next clock. This control scheme helps achieve high efficiency by scaling down the frequency to reduce the switching and gate driver losses.

As  $I_{\text{OUT}}$  increases from a light-load condition,  $V_{\text{COMP}}$  and  $f_{\text{SW}}$  both increase. If  $I_{\text{OUT}}$  exceeds the critical level while  $V_{\text{COMP}}$  is above  $V_{\text{AAM}}$ , then the MPQ2246 resumes fixed-frequency control, which is the same as FCCM (see Figure 2).

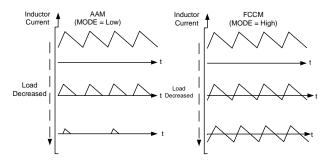


Figure 2: AAM and FCCM Operation

#### Enable (EN)

The MPQ2246 can be enabled or disabled via a remote enable (EN) signal referenced to ground. The remote EN control operates with positive logic that is compatible with popular logic devices. Positive logic implies that when  $V_{\text{IN}}$  exceeds the under-voltage lockout (UVLO) threshold (typically 2.5V), the converter is enabled by pulling EN above 1.2V. Float or ground the EN pin to disable the MPQ2246. There is an internal  $1M\Omega$  resistor connected from EN to ground.



#### Oscillator

 $f_{SW}$  can be configured via an external frequency resistor. The frequency resistor ( $R_{FREQ}$ ) should be placed between FREQ and GND, as close to the device as possible. Select the  $R_{FREQ}$  value following the  $f_{SW}$  vs.  $R_{FREQ}$  curve on page 12.

### Soft Start (SS) and Output Discharge

The MPQ2246 has soft start (SS). To avoid overshoot at start-up, SS ramps up  $V_{\text{OUT}}$  at a controlled slew rate when EN goes high.

When SS begins, an internal current source charges the external soft-start capacitor ( $C_{SS}$ ). When the SS voltage ( $V_{SS}$ ) drops below the internal reference ( $V_{REF}$ ),  $V_{SS}$  overrides  $V_{REF}$  as the EA reference. When  $V_{SS}$  exceeds  $V_{REF}$ ,  $V_{REF}$  acts as the reference. After SS finishes, the MPQ2246 enters steady state. SS can be used for tracking and sequencing.

The soft-start time ( $t_{SS}$ ) set by the external  $C_{SS}$  can be calculated with Equation (1):

$$t_{ss}(ms) = \frac{C_{ss}(nF) \times V_{REF}(V)}{I_{ss}(\mu A)}$$
(1)

Where  $C_{SS}$  is the external soft-start capacitor,  $V_{REF}$  is the internal reference voltage (0.606V), and  $I_{SS}$  is the internal soft-start charge current (4 $\mu$ A).

When SS is floating,  $t_{SS}$  is 1ms after the internal setting. The final  $t_{SS}$  is either 1ms or the external  $C_{SS}$  setting time, whichever is longer. If the MPQ2246 is disabled or experiencing an input shutdown, then the device discharges  $V_{OUT}$  to GND through an internal  $100\Omega$  resistor placed in parallel with the LS-FET.

#### **Pre-Biased Start-Up**

If  $V_{FB}$  exceeds  $V_{SS}$  (which means the output has a pre-biased voltage) at start-up, then the HS-FET and LS-FET remain off until  $V_{SS}$  exceeds  $V_{FB}$ .

#### 100% Duty Cycle

The MPQ2246 can operate with 100% duty cycle, which can extend the battery life. When  $V_{\text{IN}}$  is too low to regulate the output, the device turns the HS-FET completely on to achieve maximum  $V_{\text{OUT}}$ .

# Power Good (PG) Indicator

The MPQ2246 has power good (PG) indication. PG is the open drain of the MOSFET. When  $V_{\text{IN}}$  is present, the MOSFET turns on and PG is pulled to GND before SS is ready. If  $V_{\text{OUT}}$  is within a  $\pm\,15\%$  window of the rated voltage set by FB, then PG is pulled up to  $V_{\text{IN}}$  by an internal resistor after a set delay time. If  $V_{\text{FB}}$  moves outside of the  $\pm\,15\%$  range with a hysteresis, then the device pulls PG low to indicate an output failure status.

#### **Over-Current Protection (OCP)**

The MPQ2246 has 9A cycle-by-cycle peak current limit control.  $I_L$  is monitored while the HS-FET is on. Once  $I_L$  reaches the peak current limit ( $I_{PEAK\_LIMIT}$ ), the HS-FET turns off immediately. Then the LS-FET turns on to discharge the energy, and  $I_L$  decreases. The HS-FET does not turn on again until  $I_L$  drops below a certain current threshold, called the valley current limit ( $I_{VALLEY\_LIMIT}$ ), which prevents  $I_L$  from running away and possibly damaging the components.

When I<sub>VALLEY\_LIMIT</sub> is triggered, the over-current protection (OCP) timer starts immediately. The OCP timer is set to 100µs. If I<sub>VALLEY\_LIMIT</sub> is reached within this 100µs timeframe during each cycle, short-circuit protection (SCP) is triggered.

#### **Short-Circuit Protection (SCP)**

When a short circuit occurs, the MPQ2246 immediately reaches its current limit. Meanwhile,  $V_{\text{OUT}}$  drops until  $V_{\text{FB}}$  is below 50% of  $V_{\text{REF}}$  (0.606V). The device considers this an output dead short, and SCP immediately.

In SCP,  $I_L$  is monitored while the HS-FET is on. Once  $I_L$  reaches  $I_{PEAK\_LIMIT}$ , the HS-FET turns off immediately. Then the LS-FET turns on to discharge the energy, and  $I_L$  drops. The HS-FET does not turn on again until  $I_L$  drops below  $I_{VALLEY\_LIMIT}$ . The device repeats this operation until the short circuit disappears, and the output returns to the regulation level. This protection mode prevents  $I_L$  from running away and possibly damaging the components.

#### Over-Voltage Protection (OVP)

The MPQ2246 monitors  $V_{OUT}$  through the FB pin to detect over-voltage (OV) conditions. If  $V_{FB}$  that exceeds 115% of  $V_{REF}$  (0.606V), over-voltage protection (OVP) is triggered, and the LS-FET



turns on to discharge  $V_{OUT}$  until  $I_L$  drops to 0A. Meanwhile, the HS-FET remains off. Then the LS-FET turns off, and  $V_{OUT}$  is discharged through the internal  $100\Omega$  resistor placed in parallel with the LS-FET. The controller does not begin to switch until  $V_{OUT}$  is within regulation.

### **Under-Voltage Lockout (UVLO) Protection**

The MPQ2246 has input UVLO protection to ensure reliable output power. Assuming EN is active, the MPQ2246 starts up once  $V_{\text{IN}}$  exceeds the UVLO rising threshold. Once  $V_{\text{IN}}$  drops below the UVLO falling threshold, the device shuts down. This function prevents the device from operating at an insufficient voltage. This is a non-latch protection.

#### **Thermal Shutdown**

The MPQ2246 employs thermal protection by internally monitoring the IC temperature. This function prevents the chip from operating at exceedingly high temperatures. If the junction temperature ( $T_J$ ) exceeds the threshold value (typically 170°C), the entire chip shuts down. This is a non-latch protection. There is a 25°C hysteresis. Once  $T_J$  drops to about 145°C, the device initiates a soft start and resumes normal operation.

#### Start-Up and Shutdown

If both  $V_{\text{IN}}$  and  $V_{\text{EN}}$  exceed their respective thresholds, the chip starts up. The reference block starts first, generating a stable reference voltage and currents, and then the internal regulator is enabled. The regulator provides a stable supply for the remaining circuitries.

While the internal supply rail is up, an internal timer holds the power MOSFET off for about 50µs to blank start-up errors. If the soft-start block is enabled, it first holds its SS output low to ensure the rest of the circuitries are ready, then slowly ramps up.

Three events can shut down the chip: EN going low,  $V_{\text{IN}}$  UVLO, and thermal shutdown. During shutdown, the signaling path is blocked first to avoid any fault triggers.  $V_{\text{COMP}}$  and the internal supply rail are then pulled down. The floating driver is not subject to this shutdown command, but its charging path is disabled.



#### APPLICATION INFORMATION

#### **Setting the Output Voltage**

The external resistor divider connected to FB sets  $V_{\text{OUT}}$  (see Figure 3). The FB resistor (R4) must account for both stability and dynamic response, so it cannot be too large or too small. R5 is estimated to be  $100k\Omega$ . R6 can be calculated with Equation (2):

$$R6 = \frac{R5}{\frac{V_{OUT}}{0.606} - 1}$$
 (2)

Using a T-type feedback network is strongly recommended (see Figure 3).

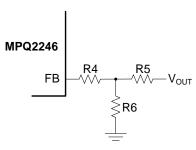


Figure 3: Feedback Network

The R5 and R4 values determine the loop bandwidth. Generally, a higher R5 + R4 value results in lower bandwidth. To ensure loop stability, it is strongly recommended to limit the bandwidth at about 10% of  $f_{\text{SW}}$ .

Table 1 lists the recommended feedback divider resistor values for common output voltages. Check the loop analysis before using in application. Change the resistance of  $R_T$  for loop stability if necessary.

Table 1: Resistances for Typical Vout

| V <sub>OUT</sub> (V) | R4 (kΩ) | R5 (kΩ)  | R6 (kΩ)   |
|----------------------|---------|----------|-----------|
| 1.2                  | 100     | 100 (1%) | 100 (1%)  |
| 1.5                  | 100     | 100 (1%) | 66.5 (1%) |
| 1.8                  | 100     | 100 (1%) | 49.9 (1%) |
| 2.5                  | 100     | 100 (1%) | 31.6 (1%) |
| 3.3                  | 100     | 100 (1%) | 22.1 (1%) |

#### Selecting the Inductor

The inductor must supply constant current to the output load while being driven by the switching  $V_{\text{IN}}$ . For a default 2.1MHz application, a 0.47 $\mu$ H to 1.5 $\mu$ H inductor is recommended.

For the highest efficiency, chose an inductor with a DC resistance below  $15m\Omega$ . A larger-value inductor results in less ripple current and a lower output ripple voltage; however, larger-value inductors are physically larger, and have a higher series resistance and/or lower saturation current.

A good rule to determine the inductance (L) is to make the inductor ripple current approximately 30% of the maximum load current. Ensure that the peak  $I_L$  is below the device peak current limit. L can be calculated with Equation (3):

$$L = \frac{V_{OUT}}{f_{SW} \times \Delta I_{L}} \times (1 - \frac{V_{OUT}}{V_{IN}})$$
(3)

Where  $\Delta I_{L}$  is the peak-to-peak inductor ripple current.

Choose an inductor that does not saturate under the maximum peak inductor current ( $I_{LP}$ ).  $I_{LP}$  can be calculated with Equation (4):

$$I_{LP} = I_{OUT} + \frac{V_{OUT}}{2f_{SW} \times L} \times (1 - \frac{V_{OUT}}{V_{IN}})$$
(4)

## Selecting the Input Capacitor

The step-down converter has a discontinuous input current, and requires a capacitor to supply the AC current to the converter while maintaining the DC  $V_{\text{IN}}$ . Use low-ESR capacitors for the best performance. Ceramic capacitors with X5R or X7R dielectrics are highly recommended due to their low ESR and small temperature coefficients. Do not use other capacitor types, such as Y5V and Z5U, because they lose too much capacitance with frequency, temperature, and bias voltage.

Place the input capacitors as close to VIN as possible. For most applications, a  $22\mu F$  capacitor is sufficient. For applications with higher  $V_{OUT}$ , use a  $47\mu F$  capacitor to improve system stability. To get a small solution size, it is recommended to choose a small package size capacitor that has a rating voltage compliant to the input specifications.

Since the input capacitor absorbs the input switching current, it requires an adequate ripple current rating. The rating should exceed the



converter's maximum input ripple current. The input ripple current ( $I_{CIN}$ ) can be calculated with Equation (5):

$$I_{CIN} = I_{OUT} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times (1 - \frac{V_{OUT}}{V_{IN}})}$$
 (5)

The worst-case condition occurs at  $V_{IN} = 2 \times V_{OUT}$ , estimated with Equation (6):

$$I_{CIN} = \frac{I_{OUT}}{2} \tag{6}$$

For simplification, choose an input capacitor with an RMS current rating that is greater than half of the maximum load current.

The input capacitor can be electrolytic, tantalum, or ceramic. When using electrolytic or tantalum capacitors, use a small, high-quality ceramic capacitor (0.1 $\mu$ F) placed as close to the IC as possible. The input capacitance determines the converter's  $V_{IN}$  ripple. If there is an  $V_{IN}$  ripple requirement in the system design, choose an input capacitor that meets the relevant specifications.

The input voltage ripple ( $\Delta V_{IN}$ ) caused by capacitance can be estimated with Equation (7):

$$\Delta V_{\text{IN}} = \frac{I_{\text{OUT}}}{f_{\text{SW}} \times C_{\text{IN}}} \times \frac{V_{\text{OUT}}}{V_{\text{IN}}} \times (1 - \frac{V_{\text{OUT}}}{V_{\text{IN}}}) \tag{7}$$

The worst-case condition occurs at  $V_{IN} = 2 \times V_{OUT}$ , calculated with Equation (8):

$$\Delta V_{IN} = \frac{1}{4} \times \frac{I_{OUT}}{f_{SW} \times C_{IN}}$$
 (8)

#### **Selecting the Output Capacitor**

The output capacitor ( $C_{\text{OUT}}$ ) maintains the DC  $V_{\text{OUT}}$ . Low-ESR ceramic capacitors are recommended for their small size and ability to keep the  $V_{\text{OUT}}$  ripple low. Electrolytic and polymer capacitors may also be used.

The output voltage ripple can be estimated with Equation (9):

$$\Delta V_{\text{OUT}} = \frac{V_{\text{OUT}}}{f_{\text{SW}} \times L} \times (1 - \frac{V_{\text{OUT}}}{V_{\text{IN}}}) \times (R_{\text{ESR}} + \frac{1}{8f_{\text{SW}} \times C_{\text{OUT}}})$$
(9)

Where  $R_{\text{ESR}}$  is the equivalent series resistance (ESR) of  $C_{\text{OUT}}$ .

For ceramic capacitors, the capacitance dominates the impedance at  $f_{SW}$  and causes the majority of  $\Delta V_{OUT}$ . For simplification, the majority of  $\Delta V_{OUT}$  can be estimated with Equation (10):

$$\Delta V_{\text{OUT}} = \frac{V_{\text{OUT}}}{8 \times f_{\text{SW}}^2 \times L \times C_{\text{OUT}}} \times (1 - \frac{V_{\text{OUT}}}{V_{\text{IN}}})$$
(10)

For tantalum or electrolytic capacitors, the ESR dominates the impedance at  $f_{SW}$ . For simplification,  $\Delta V_{OUT}$  can be calculated with Equation (11):

$$\Delta V_{\text{OUT}} = \frac{V_{\text{OUT}}}{f_{\text{SW}} \times L} \times (1 - \frac{V_{\text{OUT}}}{V_{\text{IN}}}) \times R_{\text{ESR}}$$
 (11)

When choosing the output capacitance, consider the allowable overshoot in  $V_{\text{OUT}}$  if the load is suddenly removed. In this case, the energy stored in the inductor is transferred to  $C_{\text{OUT}}$ , which causes its voltage to rise. To achieve a proper overshoot relative to the regulated voltage,  $C_{\text{OUT}}$  can be estimated with Equation (12):

$$C_{OUT} = \frac{I_{OUT}^{2} \times L}{V_{OUT}^{2} \times ((V_{OUTMAX} / V_{OUT})^{2} - 1)}$$
(12)

Where  $V_{\text{OUTMAX}}$  /  $V_{\text{OUT}}$  is the maximum allowable overshoot.

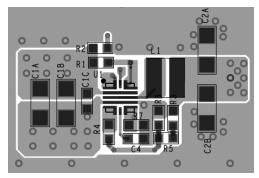
After calculating the capacitance required for both the ripple and overshoot, choose the larger of the calculated values. The characteristics of  $C_{\text{OUT}}$  also affect the stability of the regulation system. The MPQ2246 can be optimized for a wide range of capacitances and ESR values.



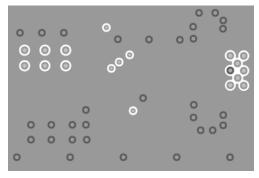
#### PCB Layout Guidelines (10)

Efficient PCB layout is critical for stable operation. A 4-layer layout is strongly recommended to improve thermal performance. For the best results, refer to Figure 4 and follow the guidelines below:

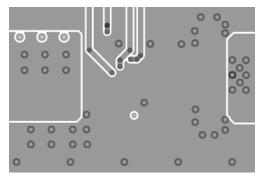
- 1. Place the high-current paths (GND, VIN, and SW) as close to the device as possible using short, direct, and wide traces.
- 2. Place the input capacitors as close to VIN as possible to reduce high-frequency noise.
- 3. Place the feedback resistor divider as close to FB as possible.
- 4. Route the FB trace away from the switching (SW) node.
- 5. Connect the bottom VIN and SW pads to a large copper area to improve thermal performance.
- 6. Use large copper areas for the power planes (VIN, SW, OUT, and GND) to reduce conduction loss and thermal stress.
- 7. Use multiple vias to connect the power planes to the internal layers.



**Top Layer** 



Mid-Layer 1



Mid-Layer 2

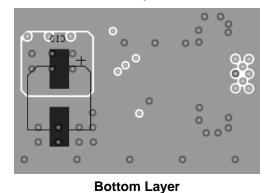


Figure 4: Recommended PCB Layout (10)

#### Note:

10) The recommended PCB layout is based on Figure 5 on page 25



# TYPICAL APPLICATION CIRCUITS

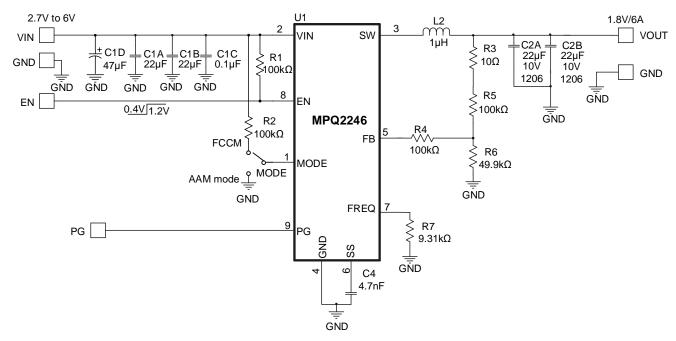


Figure 5: Typical Application Circuit (Vout = 1.8V, lout = 6A)

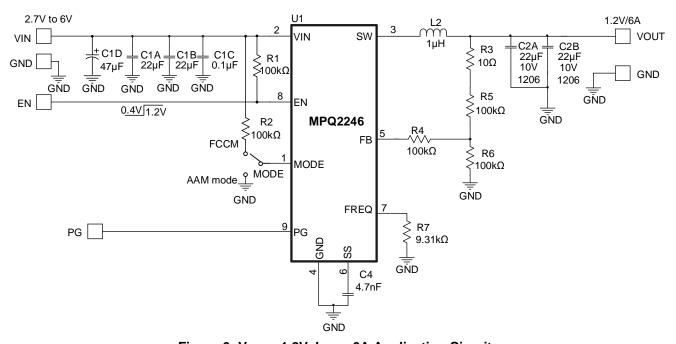
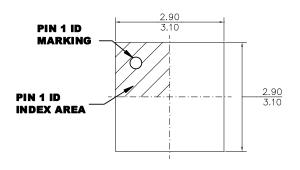


Figure 6: V<sub>OUT</sub> = 1.2V, I<sub>OUT</sub> = 6A Application Circuit

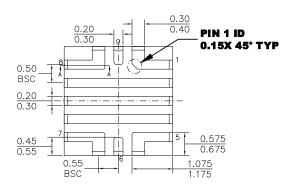


# **PACKAGE INFORMATION**

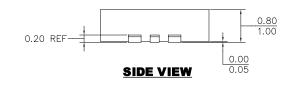
# QFN-9 (3mmx3mm)

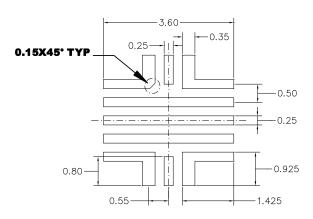




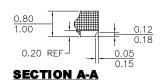


**BOTTOM VIEW** 





**RECOMMENDED LAND PATTERN** 

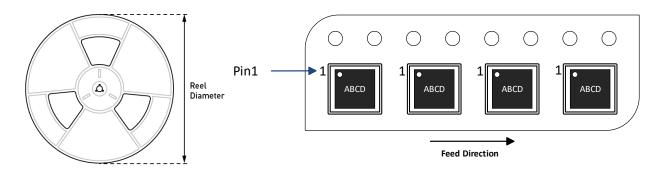


#### **NOTE:**

- 1) THE LEAD SIDE IS WETTABLE.
- 2) ALL DIMENSIONS ARE IN MILLIMETERS.
- 3) LEAD COPLANARITY SHALL BE 0.08 MILLIMETERS MAX.
- 4) JEDEC REFERENCE IS MO-220.
- 5) DRAWING IS NOT TO SCALE.



# **CARRIER INFORMATION**



| Part Number           | Package<br>Description | Quantity/<br>Reel | Quantity/<br>Tube | Quantity/<br>Tray | Reel<br>Diameter | Carrier<br>Tape<br>Width | Carrier<br>Tape<br>Pitch |
|-----------------------|------------------------|-------------------|-------------------|-------------------|------------------|--------------------------|--------------------------|
| MPQ2246GQE-<br>AEC1-Z | QFN-9<br>(3mmx3mm)     | 5000              | N/A               | N/A               | 13in             | 12mm                     | 8mm                      |



# **REVISION HISTORY**

| Revision # | Revision Date | Description     | Pages Updated |
|------------|---------------|-----------------|---------------|
| 1.0        | 11/15/2022    | Initial Release | -             |

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